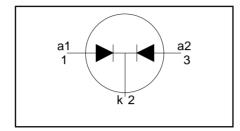
## PBYR645CT series

## **FEATURES**

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- Low thermal resistance

## **SYMBOL**



## QUICK REFERENCE DATA

$$V_R = 35 \text{ V/ } 40 \text{ V/ } 45 \text{ V}$$

$$I_{O(AV)} = 10 \text{ A}$$

$$V_F \le 0.6 \text{V}$$

## **GENERAL DESCRIPTION**

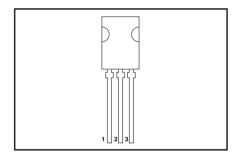
Dual, common cathode schottky rectifier diodes in a plastic envelope. Intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR645CT series is supplied in the conventional leaded SOT82 package.

## **PINNING**

PIN	DESCRIPTION		
1	anode 1		
2	cathode		
3	anode 2		
tab	cathode		

#### SOT82



## **LIMITING VALUES**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.		MAX.		UNIT
		PBYR6		35CT	40CT	45CT	
$V_{RRM}$	Peak repetitive reverse voltage		-	35	40	45	V
$V_{RWM}$	Working peak reverse voltage		-	35	40	45	V
$V_R$	Continuous reverse voltage	T <sub>mb</sub> ≤ 100 °C	-	35	40	45	V
I <sub>O(AV)</sub>	Average rectified output current (both diodes conducting)	square wave; $\delta = 0.5$ ; $T_{mb} \le 119$ °C	-		10		Α
I <sub>FRM</sub>	Repetitive peak forward current per diode	square wave; $\delta = 0.5$ ; $T_{mb} \le 119 ^{\circ}C$	-		10		Α
I <sub>FSM</sub>	Non-repetitive peak forward current diode	t = 10  ms t = 8.3  ms sinusoidal; $T_i = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$	-		75 82		A A
I <sub>RRM</sub>	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T <sub>i max</sub>	-		1		Α
T <sub>j</sub>	Operating junction temperature	Jillax	-		150		°C
$T_{stg}$	Storage temperature		- 65		150		Ç

## THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R <sub>th i-a</sub>	to mounting base	per diode both diodes in free air	1 1 1	- - 100	5 4 -	K/W K/W K/W

PBYR645CT series

# **ELECTRICAL CHARACTERISTICS**

 $T_j = 25$  °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{F}$	Forward voltage	$I_F = 5 \text{ A}; T_i = 125^{\circ}\text{C}$	-	0.51	0.6	V
		$I_{\rm F} = 10  {\rm A}^{\circ}$	-	0.72	0.87	V
I <sub>R</sub>	Reverse current	$V_R = V_{RWM}$	-	0.12	0.5	mΑ
		$V_{R} = V_{RWM}$ ; $T_{j} = 100^{\circ}C$	-	10	15	mΑ
C <sub>d</sub>	Junction capacitance	$V_R = 5 \text{ W}$ ; $f = 1 \text{ MHz}$ , $T_j = 25 \text{ C}$ to $125 \text{ C}$	-	150	-	pF

## PBYR645CT series

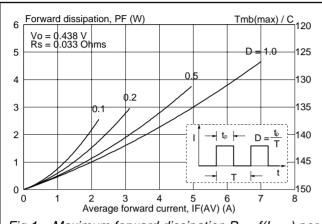


Fig.1. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; square current waveform where  $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$ .

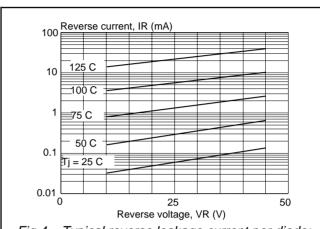


Fig.4. Typical reverse leakage current per diode;  $I_R = f(V_R)$ ; parameter  $T_j$ 

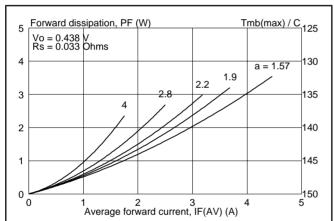


Fig.2. Maximum forward dissipation  $P_F = f(I_{F(AV)})$  per diode; sinusoidal current waveform where a = form factor  $= I_{F(RMS)} / I_{F(AV)}$ .

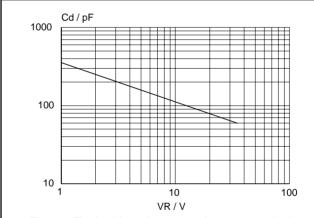


Fig.5. Typical junction capacitance per diode;  $C_d = f(V_R)$ ; f = 1 MHz;  $T_j = 25$ °C to 125°C.

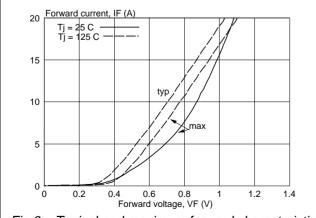
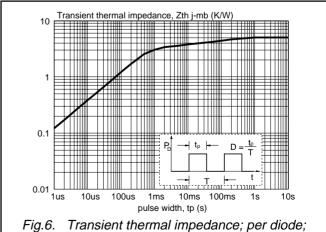


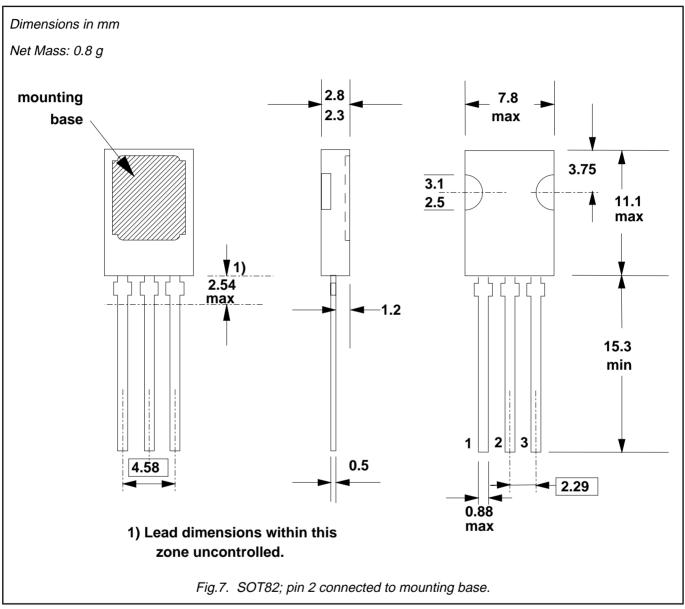
Fig.3. Typical and maximum forward characteristic  $I_F = f(V_F)$ ; parameter  $T_i$ 



rig.6. Transient thermal impedance; per diode;  $Z_{th j\text{-}mb} = f(t_p)$ .

PBYR645CT series

## **MECHANICAL DATA**



#### **Notes**

- Refer to mounting instructions for SOT82 envelopes.
   Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

## Rectifier diodes Schottky barrier

PBYR645CT series

#### **DEFINITIONS**

Data sheet status					
Objective specification This data sheet contains target or goal specifications for product development.					
Preliminary specification This data sheet contains preliminary data; supplementary data may be published la					
Product specification This data sheet contains final product specifications.					
Limiting values					

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

#### **Application information**

Where application information is given, it is advisory and does not form part of the specification.

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